



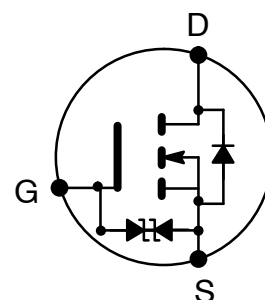
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NTE2926 **MOSFET** **N-Ch, Enhancement Mode** **High Speed Switch** **TO3PN Type Package**

Features:

- Good Frequency Characteristic
- High Speed Switching
- Wide Area of Safe Operation
- Enhancement Mode
- Good Complementary Characteristics
- Equipped with Gate Protection Diodes
- Suitable for Audio Power Amplifier



Absolute Maximum Ratings:

Drain-Source Voltage, V_{DSX}	160V
Gate-Source Voltage, V_{GSS}	± 15
Drain Current, I_D	7A
Body-to-Drain Diode Reverse Drain Current, I_{DR}	7A
Channel Dissipation ($T_C = +25^{\circ}\text{C}$), P_{ch}	100W
Channel Temperature, T_{ch}	$+150^{\circ}\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^{\circ}\text{C}$

Electrical Characteristics: ($T_A = +25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSX}$	$V_{GS} = -10\text{V}$, $I_D = 10\text{mA}$	160	–	–	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$V_{DS} = 0\text{V}$, $I_G = \pm 100\mu\text{A}$	± 15	–	–	V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10\text{V}$, $I_D = 100\text{mA}$	0.15	–	1.45	V
Drain-Source Saturation Voltage	$V_{DS(sat)}$	$V_{GD} = 0\text{V}$, $I_D = 7\text{A}$, Note 1	–	–	12	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10\text{V}$, $I_D = 3\text{A}$, Note 1	0.7	1.0	1.4	S
Input Capacitance	C_{iss}	$V_{GS} = -5\text{V}$, $V_{DS} = 10\text{V}$, $f = 1\text{MHz}$	–	600	–	pF
Output Capacitance	C_{oss}		–	350	–	pF
Reverse Transfer Capacitance	C_{rss}		–	10	–	pF
Turn-On Time	t_{on}	$V_{DD} = 20\text{V}$, $I_D = 4\text{A}$	–	180	–	ns
Turn-Off Time	t_{off}		–	60	–	ns

Note 1. Pulse test.

